

1. Base 2. Collector 3. Emitter

PNP Silicon Darlington Transistor

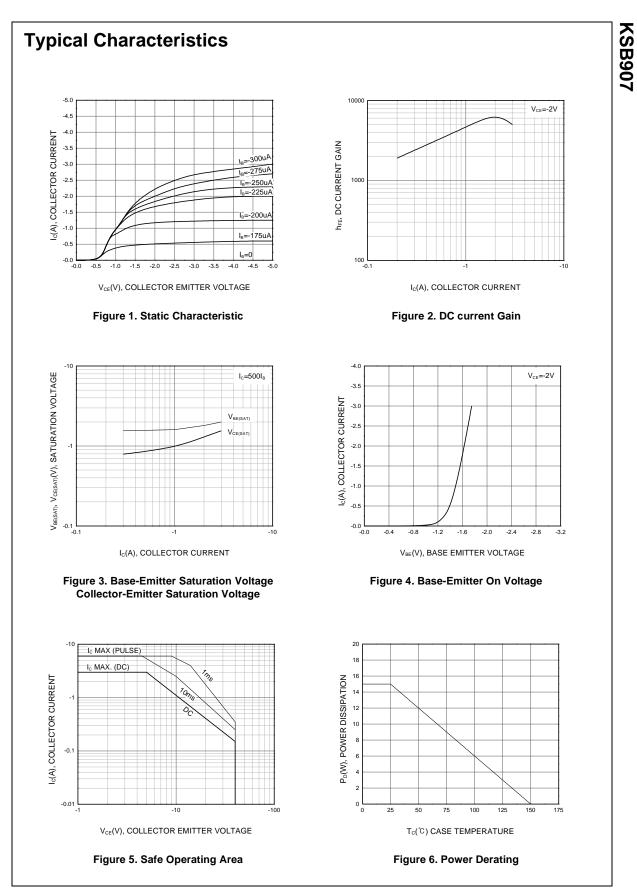
Absolute Maximum Ratings $T_{C}=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	- 60	V
V _{CEO}	Collector-Emitter Voltage	- 40	V
V _{EBO}	Emitter-Base Voltage	- 5	V
I _C	Collector Current(DC)	- 3	А
I _B	Base Current	- 0.3	А
P _C	Collector Dissipation (T _a =25°C)	15	W
P _C P _C	Collector Dissipation (T _C =25°C)	1	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

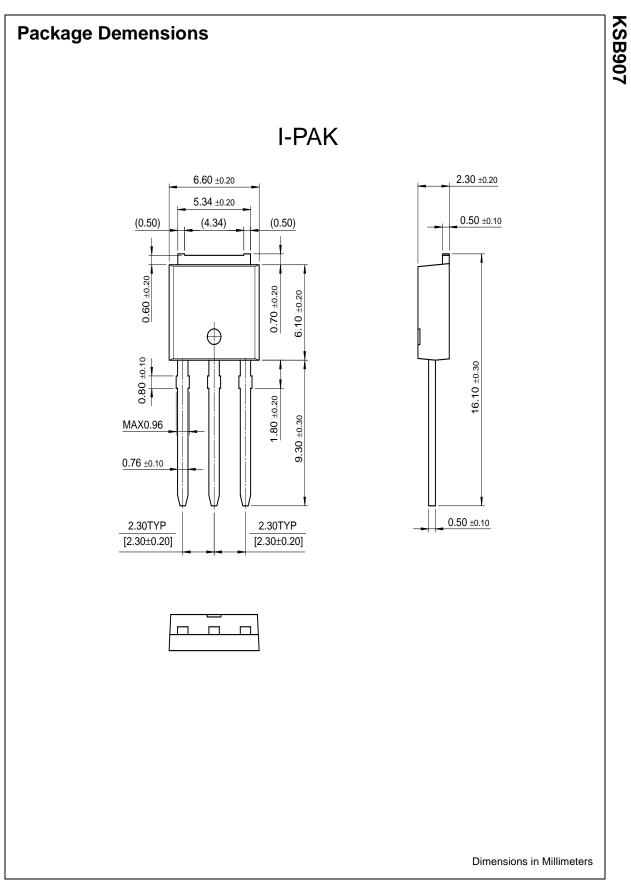
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector- Emitter Breakdown Voltage	I _C = - 25mA, I _B = 0	- 40			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -60V, I_E = 0$			- 20	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2.5	μA
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} = - 2V, I _C = - 1A V _{CE} = - 2V, I _C = - 3A	2000 1000			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = - 2A, I _B = - 4mA			- 1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = - 2A, I _B = - 4mA			- 2	V
t _{ON}	Turn ON Time	V _{CC} = - 30V, I _C = - 3A		0.3		μs
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = -6mA$		0.6		μs
t _F	Fall Time	$R_L = 10\Omega$		0.25		μs

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